

US-CL-CURRENT: 117/103; 117/84, 257/E21.127, 257/E21.131

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Draw. Data
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Jan 29, 2004

1010161396

PUBLICATION-DATE: January 29, 2004

NAME	CITY	STATE	COUNTRY	RULE-47
<u>Nagai</u> , Seiji	Nishikasugai-gun		JP	
Kojima, Akira	Nishikasugai-gun		JP	
Tomita, Kazuyoshi	Nagoya-shi		JP	

US-CL-CURRENT: (~~147/84~~), 257/E21.113, 257/E21.127, 257/E21.131

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Draw D.
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Jul 17, 2003

TITLE: Production method of III nitride compound semiconductor and III nitride compound semiconductor element

PUBLICATION-DATE: July 17, 2003

NAME	CITY	STATE	COUNTRY	RULE-47
Koike, Masayoshi	Nishikasugai-gun		JP	
Tezen, Yuta	Nishikasugai-gun		JP	
Yamashita, Hiroshi	Nishikasugai-gun		JP	
<u>Nagai</u> , Seiji	Nishikasugai-gun		JP	
Hiramatsu, Toshio	Nishikasugai-gun		JP	

US-CL-CURRENT: 438/41; 257/E21.131

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Draw D
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☐ 5. Document ID: US 20030124789 A1

L7: Entry 5 of 34

File: PGPB

Jul 3, 2003

PGPUB-DOCUMENT-NUMBER: 20030124789  
PGPUB-FILING-TYPE: new  
DOCUMENT-IDENTIFIER: US 20030124789 A1

TITLE: Semiconductor light-emitting device and manufacturing method thereof

PUBLICATION-DATE: July 3, 2003

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koide, Norikatsu	Aichi		JP	
Asami, Shinya	Aichi		JP	
Umezaki, Junichi	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Yamasaki, Shiro	Aichi		JP	
<u>Nagai</u> , Seiji	Aichi		JP	

US-CL-CURRENT: 438/200; 257/E29.078, 257/E33.008, 257/E33.028

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Draw D
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☐ 6. Document ID: US 20030010281 A1

L7: Entry 6 of 34

File: PGPB

Jan 16, 2003

PGPUB-DOCUMENT-NUMBER: 20030010281  
PGPUB-FILING-TYPE: new  
DOCUMENT-IDENTIFIER: US 20030010281 A1

TITLE: Semiconductor substrate

PUBLICATION-DATE: January 16, 2003

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koike, Masayoshi	Nishikasugai-gun		JP	
<u>Nagai</u> , Seiji	Nishikasugai-gun		JP	

US-CL-CURRENT: 117/97

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Draw D
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☐ 7. Document ID: US 20020179005 A1

L7: Entry 7 of 34

File: PGPB

Dec 5, 2002

PGPUB-DOCUMENT-NUMBER: 20020179005  
PGPUB-FILING-TYPE: new  
DOCUMENT-IDENTIFIER: US 20020179005 A1

~~10/18/02~~  
10/18/02 005

TITLE: Method for manufacturing group III nitride compound semiconductor and a light-emitting device using group III nitride compound semiconductor

PUBLICATION-DATE: December 5, 2002

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koike, Masayoshi	Aichi-ken		JP	
Nagai, Seiji	Aichi-ken		JP	

US-CL-CURRENT: 117/84; 257/E21.113, 257/E21.125

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Draw D
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☐ 8. Document ID: US 20020146854 A1

L7: Entry 8 of 34

File: PGPB

Oct 10, 2002

PGPUB-DOCUMENT-NUMBER: 20020146854  
PGPUB-FILING-TYPE: new  
DOCUMENT-IDENTIFIER: US 20020146854 A1

TITLE: Semiconductor light-emitting device and manufacturing method thereof

PUBLICATION-DATE: October 10, 2002

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koide, Norikatsu	Aichi		JP	
Asami, Shinya	Aichi		JP	
Umezaki, Junichi	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Yamasaki, Shiro	Aichi		JP	
Nagai, Seiji	Aichi		JP	

US-CL-CURRENT: 438/22; 257/E29.078, 257/E33.008, 257/E33.028

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC	Draw D
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☐ 9. Document ID: US 20020006726 A1

L7: Entry 9 of 34

File: PGPB

Jan 17, 2002

PGPUB-DOCUMENT-NUMBER: 20020006726  
PGPUB-FILING-TYPE: new  
DOCUMENT-IDENTIFIER: US 20020006726 A1

TITLE: METHOD FOR MANUFACTURING GROUP III NITRIDE COMPOUND SEMICONDUCTOR LASER  
DIODES

PUBLICATION-DATE: January 17, 2002

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
YAMASAKI, SHIRO	INAZAWA-SHI		JP	
<u>NAGAI</u> , SEIJI	NAGOYA-SHI		JP	
KOIKE, MASAYOSHI	ICHINOMIYA-SHI		JP	
AKASAKI, ISAMU	NAGOYA-SHI		JP	
AMANO, HIROSHI	NAGOYA-SHI		JP	
YAMADA, ISAO	HIMEJI-SHI		JP	
MASUO, JIRO	KYOTO-SHI		JP	

US-CL-CURRENT: 438/689

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Draw D
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☐ 10. Document ID: US 20010048112 A1

L7: Entry 10 of 34

File: PGPB

Dec 6, 2001

PGPUB-DOCUMENT-NUMBER: 20010048112  
PGPUB-FILING-TYPE: new  
DOCUMENT-IDENTIFIER: US 20010048112 A1

TITLE: Semiconductor light-emitting device and manufacturing method thereof

PUBLICATION-DATE: December 6, 2001

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Koide, Norikatsu	Aichi		JP	
Asami, Shinya	Aichi		JP	
Umezaki, Junichi	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Yamasaki, Shiro	Aichi		JP	
<u>Nagai</u> , Seiji	Aichi		JP	

US-CL-CURRENT: 257/94; 257/104, 257/E29.078, 257/E33.008, 257/E33.028

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC	Draw D
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*Inventor  
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☐ 1. Document ID: US 20040219702 A1

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L7: Entry 1 of 34

File: PGPB

Nov 4, 2004

PGPUB-DOCUMENT-NUMBER: 20040219702

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040219702 A1

*10/21/02*

TITLE: Method for manufacturing group-III nitride compound semiconductor, and group-III nitride compound semiconductor device

PUBLICATION-DATE: November 4, 2004

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
<u>Nagai</u> , Seiji	Aichi		JP	
Koike, Masayoshi	Aichi		JP	
Tomita, Kazuyoshi	Aichi		JP	

US-CL-CURRENT: 438/46; 438/47, 438/478, 438/481

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	WAC	Draw D
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☐ 2. Document ID: US 20040123796 A1

L7: Entry 2 of 34

File: PGPB

Jul 1, 2004

PGPUB-DOCUMENT-NUMBER: 20040123796

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040123796 A1

TITLE: Production method for semiconductor crystal and semiconductor luminous element

PUBLICATION-DATE: July 1, 2004

## INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
<u>Nagai</u> , Seiji	Aichi		JP	
Tomita, Kazuyoshi	Aichi		JP	
Yamazaki, Shiro	Aichi		JP	